

MICRO ELECTRONICS CRO

2N3417

NPN

SILICON
TRANSISTOR

2N3417 is NPN silicon planar transistor designed for general purpose AF medium power applications.

TO-92



ECB

ABSOLUTE MAXIMUM RATINGS

| | | |
|---------------------------|----------|---------------|
| Collector-Base Voltage | VCBO | 50V |
| Collector-Emitter Voltage | VCEO | 50V |
| Emitter-Base Voltage | VEBO | 5V |
| Collector Current | IC | 500mA |
| Total Power Dissipation | Tj, Tstg | -55 to +150°C |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| PARAMETER | SYMBOL | MIN | MAX | UNIT | TEST CONDITIONS |
|--------------------------------------|----------|-----|------|------|--------------------------|
| Collector-Base Breakdown Voltage | BVCBO | 50 | | V | IC=100µA IE=0 |
| Collector-Emitter Breakdown Voltage | BVCEO | 50 | | V | IC=10mA IB=0 |
| Emitter-Base Breakdown Voltage | BVEBO | 5 | | V | IE=10µA IC=0 |
| Collector Cutoff Current | ICBO | | 100 | nA | VCB=50V IE=0 |
| Emitter Cutoff Current | IEBO | | 100 | nA | VEB=5V IC=0 |
| D.C. Current Gain | HFE | 180 | 540 | | IC=2mA VCE=4.5V |
| Collector-Emitter Saturation Voltage | VCE(sat) | | 0.3 | V | IC=50mA IB=3mA |
| Base-Emitter Saturation Voltage | VBE(sat) | | 0.85 | V | IC=50mA IB=3mA |
| Small Signal Current Gain | hfe | 300 | TYP | | IC=1mA VCE=10V f=1KHz |

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